EAST Search History

10/596380

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/596380	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/14 20:36
L2	5	("5589694").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/14 20:41
L3	1	"5488000".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:37
L4	1	"5426064".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:37
L5	1	"5418389".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:37
L6	1	"5275851".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:37
L7	1	"5229625".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:37
L8	1	"5147826".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:37
L9	1	"4912061".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:38
L10	1	"4894699".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:38
L11	1	"4769686".PN.	USPAT; USOCR	OR	OFF	2007/12/14 20:38
L12	2	(polycrystalline adj silicon adj islands) and channel and doped and source and drain and (thin adj film adj transistor) and (pin adj diode) and (amorphous adj silicon adj intrinsic adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/14 20:45
L13	3	(polycrystalline adj silicon) and channel and doped and source and drain and (thin adj film adj transistor) and (pin adj diode) and (amorphous adj silicon adj intrinsic adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/14 20:47

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L14	2	("20060030084").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/14 20:47
L15	2	14 and (pin or diode or amorphous or silicon polycrystalline or island or plurality or channel or region or source or drain or doped or thin or film ot transistor or intrinsic or n-type or p-type or separated or contacts or overlies)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/14 20:50